



20V, P-Channel NexFET™ Power MOSFETs

Check for Samples: [CSD25481F4](#)

FEATURES

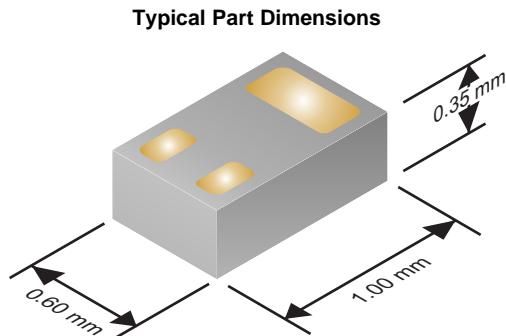
- Ultra Low On Resistance
- Ultra Low Q_g and Q_{gd}
- High Operating Drain Current
- Ultra Small Footprint (0402 Case Size)
 - 1.0 mm x 0.6 mm
- Ultra Low Profile
 - 0.35 mm Max Height
- Integrated ESD Protection Diode
 - Rated > 4kV HBM
 - Rated > 2kV CDM
- Pb Free Terminal Plating and Halogen Free
- RoHS Compliant

APPLICATIONS

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching Applications
- Battery Applications
- Handheld and Mobile Applications

DESCRIPTION

This 90mΩ, 20V P-Channel FemtoFET™ MOSFET has been designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.



Typical Part Dimensions

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	-20		V
Q_g	Gate Charge Total (-4.5V)	913		pC
Q_{gd}	Gate Charge Gate to Drain	153		pC
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = -1.8V$	395	mΩ
		$V_{GS} = -2.5V$	145	mΩ
		$V_{GS} = -4.5V$	90	mΩ
$V_{GS(th)}$	Threshold Voltage	-0.95		V

ORDERING INFORMATION

Device	Qty	Media	Package	Ship
CSD25481F4	3,000	7-Inch Reel	Femto(0402) 1.0mm x 0.6mm Land Grid Array (LGA)	Tape and Reel
CSD25481F4R	18,000	13-Inch Reel		

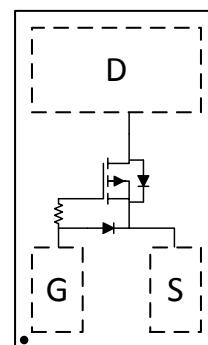
ABSOLUTE MAXIMUM RATINGS

	$T_A = 25^\circ\text{C}$ unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	-20	V
V_{GS}	Gate to Source Voltage	-12	V
I_D	Continuous Drain Current ⁽¹⁾	-2.5	A
I_{DM}	Pulsed Drain Current ⁽²⁾	-10	A
P_D	Power Dissipation ⁽¹⁾	500	mW
ESD Rating	Human Body Model (HBM) Charged Device Model (CDM)	4 2	kV
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

(1) Typical $R_{DS(on)} = 85^\circ\text{C}/\text{W}$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.

(2) Pulse duration $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

Top View



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FemtoFET is a trademark of Texas Instruments.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	$V_{\text{GS}} = 0\text{V}$, $I_{\text{DS}} = -250\mu\text{A}$		-20		V
I_{DSS}	Drain to Source Leakage Current	$V_{\text{GS}} = 0\text{V}$, $V_{\text{DS}} = -16\text{V}$			-1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{\text{DS}} = 0\text{V}$, $V_{\text{GS}} = -12\text{V}$			-100	nA
$V_{\text{GS}(\text{th})}$	Gate to Source Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{DS}} = -250\mu\text{A}$	-0.70	-0.95	-1.20	V
$R_{\text{DS}(\text{on})}$	Drain to Source On Resistance	$V_{\text{GS}} = -1.8\text{V}$, $I_{\text{DS}} = -0.1\text{A}$		395	800	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}$, $I_{\text{DS}} = -0.5\text{A}$		145	174	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}$, $I_{\text{DS}} = -0.5\text{A}$		90	105	$\text{m}\Omega$
		$V_{\text{GS}} = -8\text{V}$, $I_{\text{DS}} = -0.5\text{A}$		75	88	$\text{m}\Omega$
g_{fs}	Transconductance	$V_{\text{DS}} = -10\text{V}$, $I_{\text{DS}} = -0.5\text{A}$		3.3		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{GS}} = 0\text{V}$, $V_{\text{DS}} = -10\text{V}$, $f = 1\text{MHz}$		189		pF
C_{oss}	Output Capacitance			78		pF
C_{rss}	Reverse Transfer Capacitance			5.5		pF
R_{G}	Series Gate Resistance			20		Ω
Q_g	Gate Charge Total (4.5V)	$V_{\text{DS}} = -10\text{V}$, $I_{\text{DS}} = -0.5\text{A}$		913		pC
Q_{gd}	Gate Charge Gate to Drain			153		pC
Q_{gs}	Gate Charge Gate to Source			240		pC
$Q_{\text{g}(\text{th})}$	Gate Charge at V_{th}			116		pC
Q_{oss}	Output Charge		$V_{\text{DS}} = -10\text{V}$, $V_{\text{GS}} = 0\text{V}$	1030		pC
$t_{\text{d}(\text{on})}$	Turn On Delay Time	$V_{\text{DS}} = 0\text{V}$, $V_{\text{GS}} = -4.5\text{V}$, $I_{\text{DS}} = -0.5\text{A}$, $R_{\text{G}} = 2\Omega$		4.1		ns
t_r	Rise Time			3.6		ns
$t_{\text{d}(\text{off})}$	Turn Off Delay Time			16.9		ns
t_f	Fall Time			6.7		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_{\text{SD}} = -0.5\text{A}$, $V_{\text{GS}} = 0\text{V}$		-0.75		V
Q_{rr}	Reverse Recovery Charge	$V_{\text{DS}} = -10\text{V}$, $I_{\text{F}} = -0.5\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		1,010		pC
t_{rr}	Reverse Recovery Time			7.5		ns

THERMAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		Typical Values	UNIT
$R_{\theta\text{JA}}$	Thermal Resistance Junction to Ambient ⁽¹⁾	85	$^\circ\text{C}/\text{W}$
	Thermal Resistance Junction to Ambient ⁽²⁾	245	$^\circ\text{C}/\text{W}$

(1) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 (2) Device mounted on FR4 material with minimum Cu mounting area.

TYPICAL MOSFET CHARACTERISTICS

$(T_A = 25^\circ\text{C}$ unless otherwise stated)

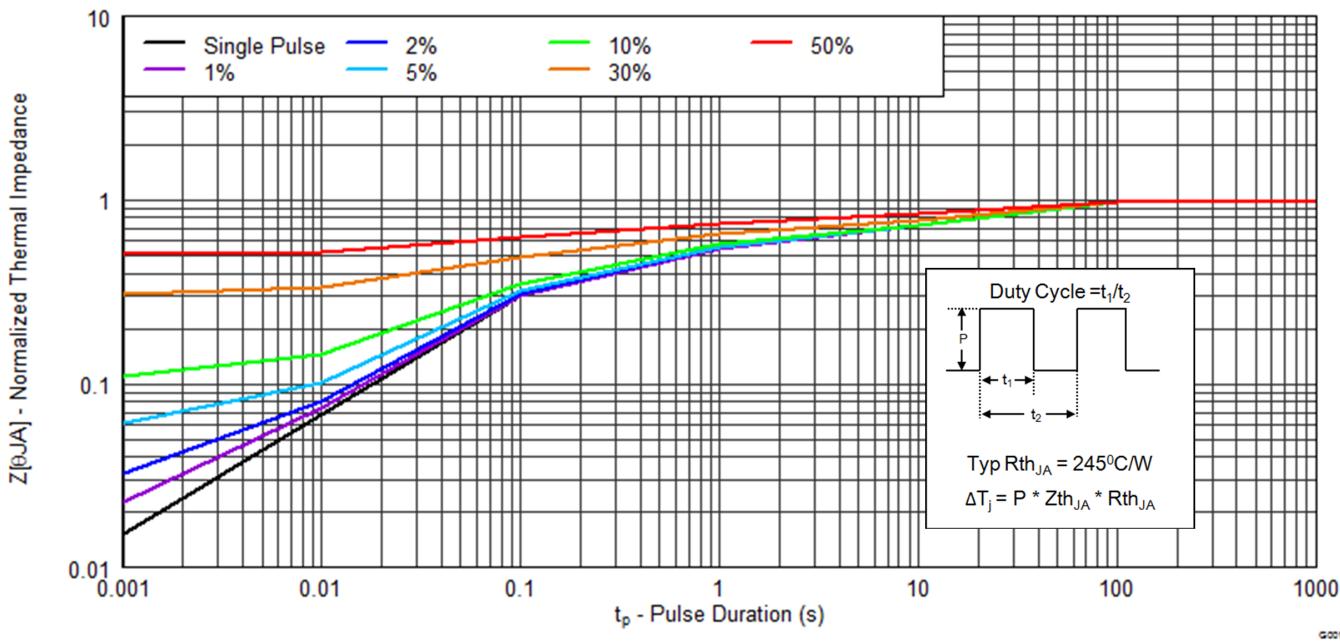


Figure 1. Transient Thermal Impedance

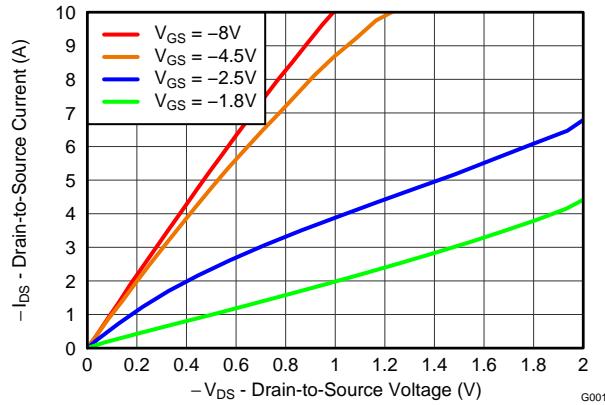


Figure 2. Saturation Characteristics

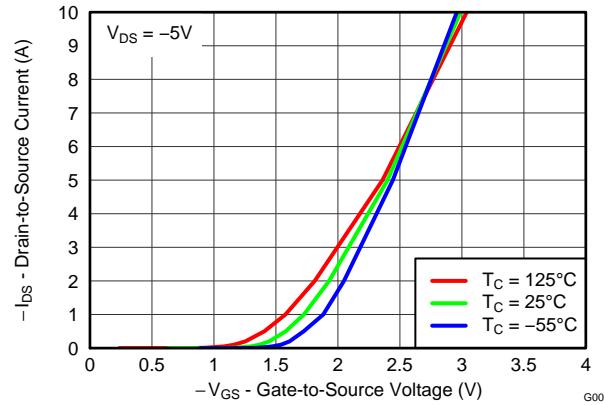


Figure 3. Transfer Characteristics

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

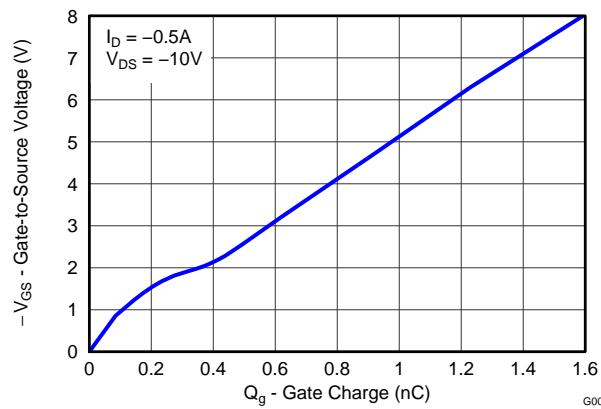


Figure 4. Gate Charge

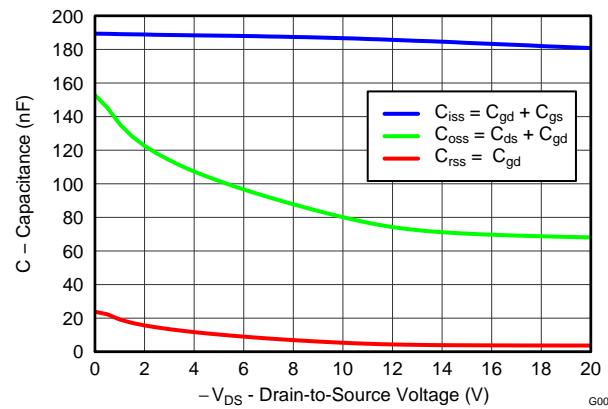


Figure 5. Capacitance

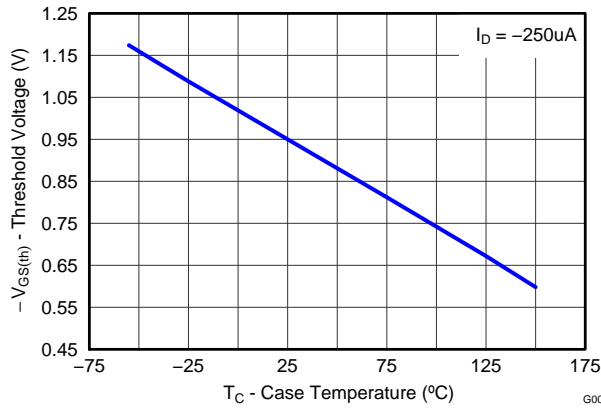


Figure 6. Threshold Voltage vs. Temperature

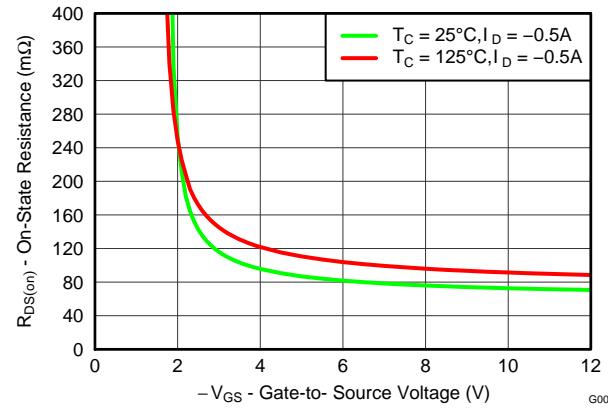


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

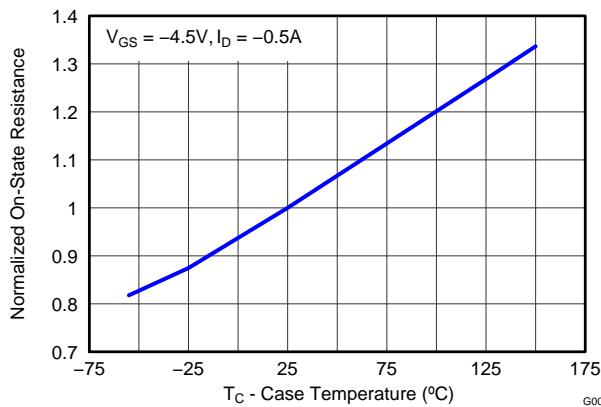


Figure 8. Normalized On-State Resistance vs. Temperature

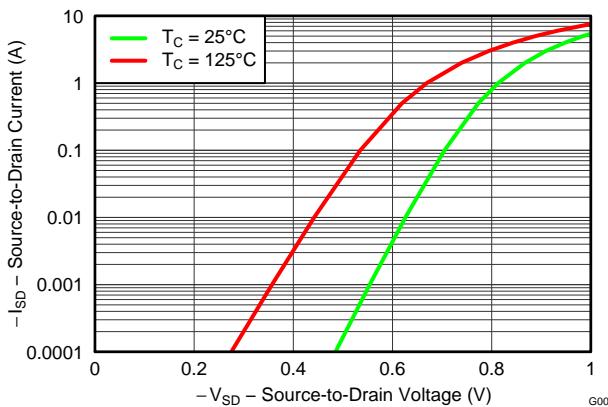


Figure 9. Typical Diode Forward Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

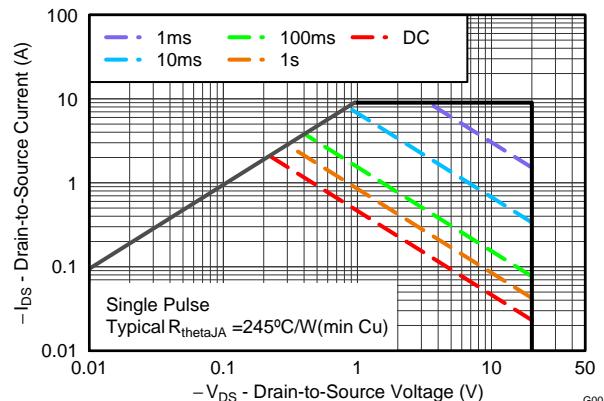


Figure 10. Maximum Safe Operating Area

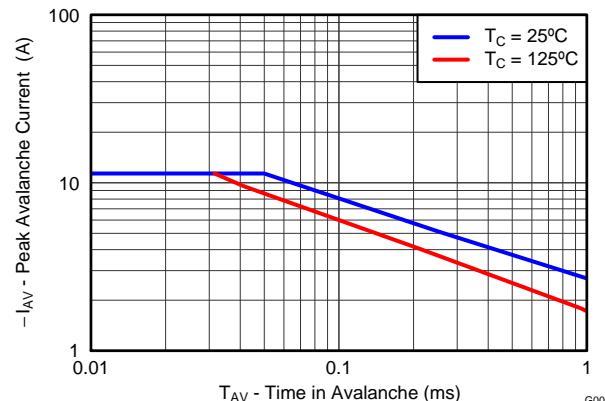


Figure 11. Single Pulse Unclamped Inductive Switching

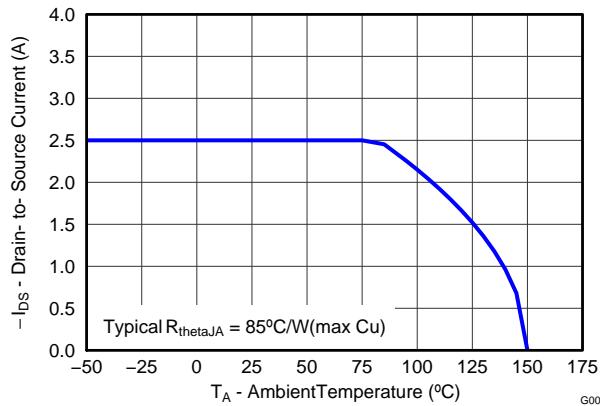
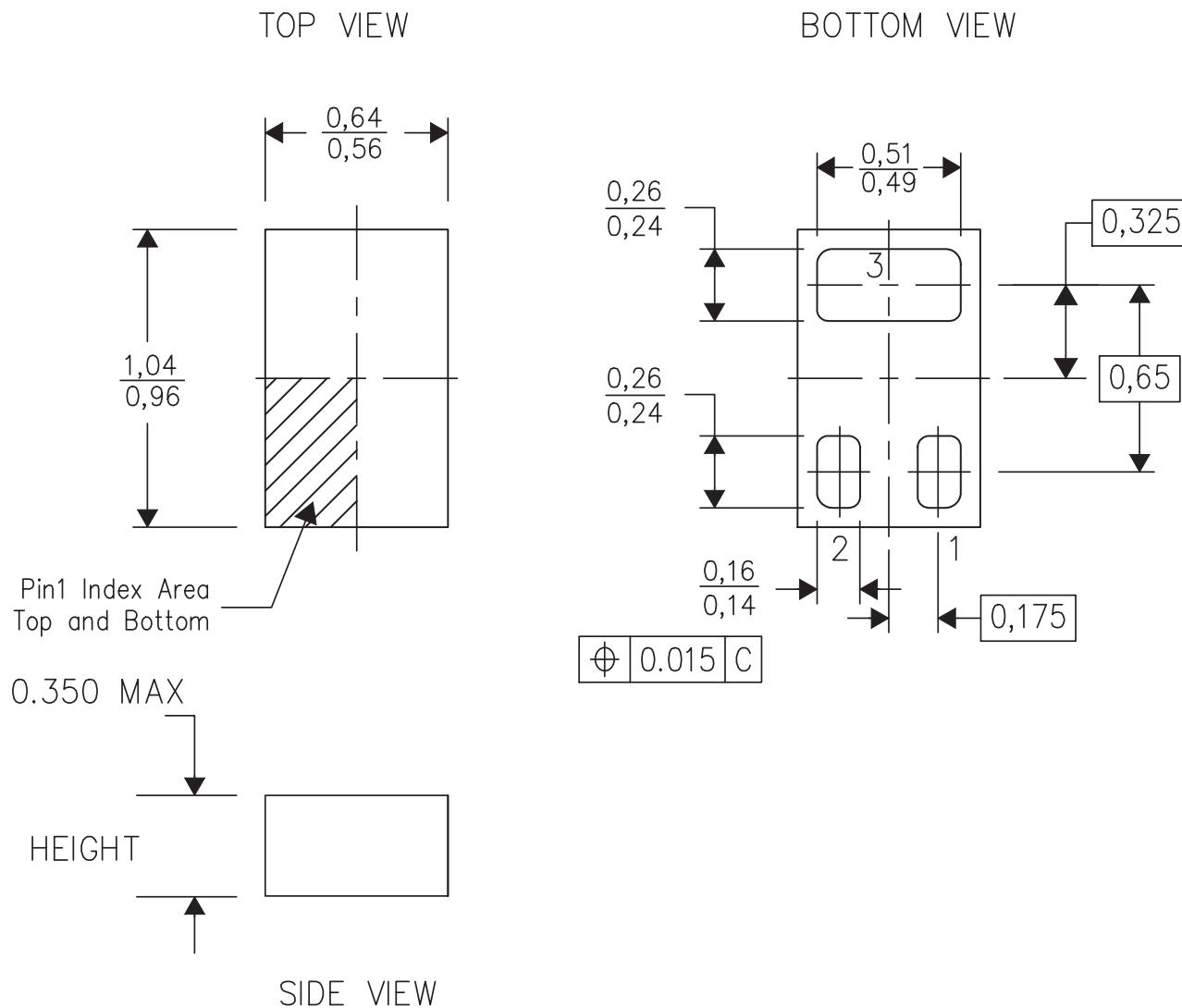


Figure 12. Maximum Drain Current vs. Temperature

MECHANICAL DATA

0402 Mechanical Dimensions

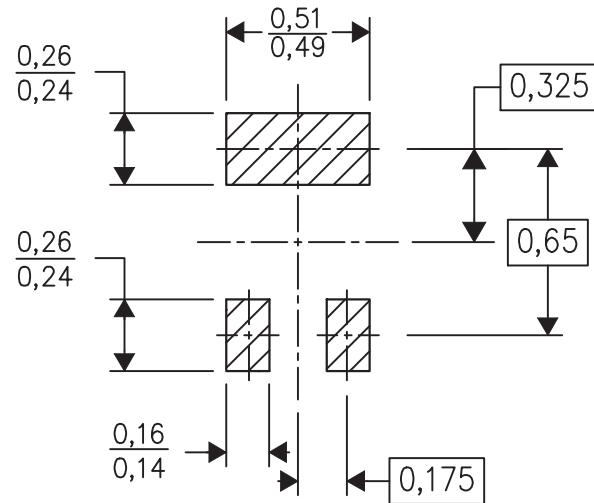


- (1) All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994)
- (2) This drawing is subject to change without notice
- (3) This package is a PB-Free solder land design

Table 1. Pin Configuration

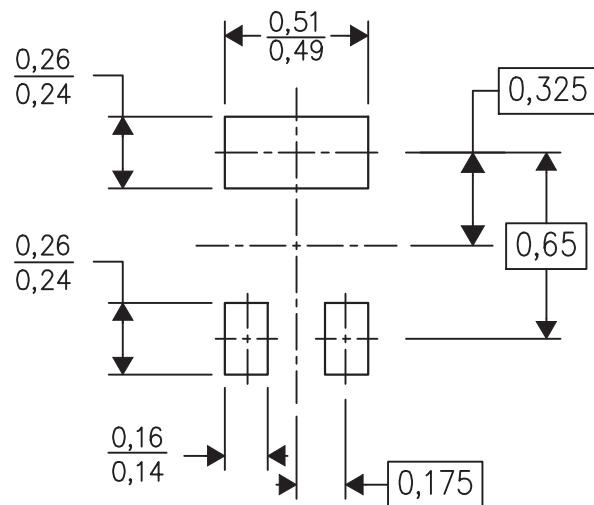
Position	Designation
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

Recommended Minimum PCB Layout



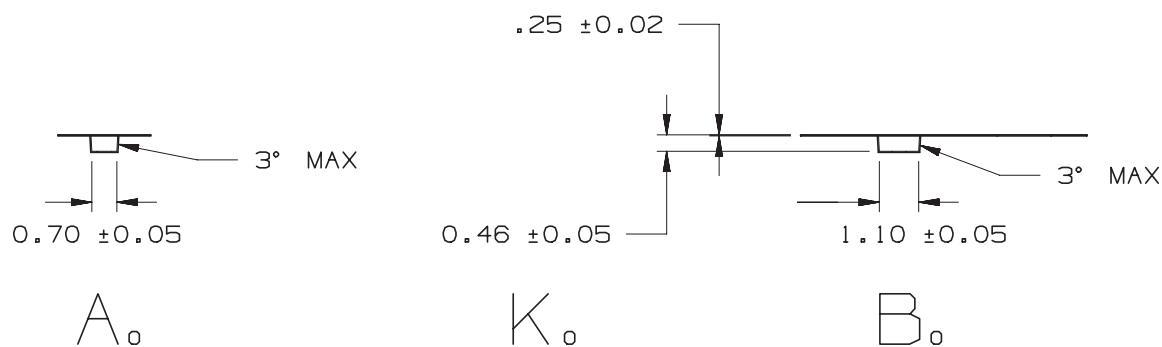
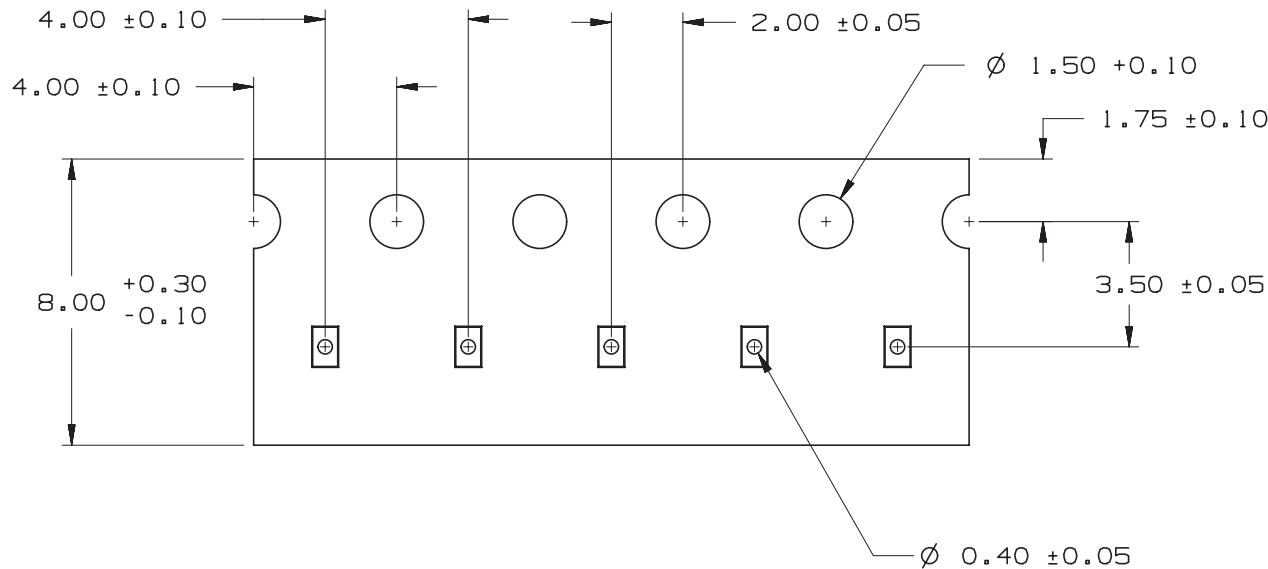
(1) All dimensions are in millimeters.

Recommended Stencil Pattern



(1) All dimensions are in millimeters.

CSD17381F4 Embossed Carrier Tape Dimensions



(1) Pin 1 will be oriented in the top right quadrant of the tape enclosure (Quadrant 2), closest to the carrier tape sprocket holes.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD25481F4	ACTIVE	PICOSTAR	YJC	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-250C-UNLIM	-40 to 85	CS	Samples
CSD25481F4R	PREVIEW	PICOSTAR	YJC	3	18000	TBD	Call TI	Call TI	-40 to 85		

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

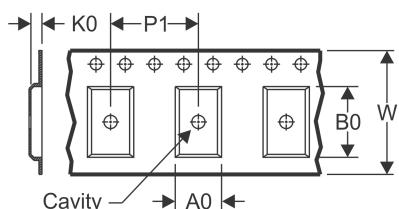
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

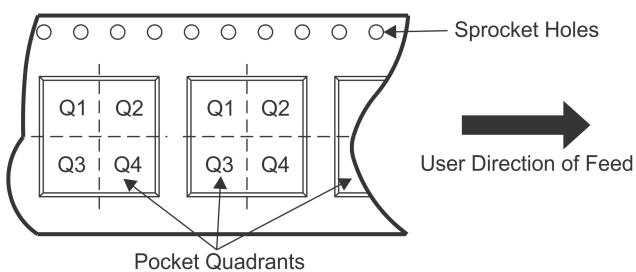
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TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25481F4	PICOST AR	YJC	3	3000	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD25481F4	PICOSTAR	YJC	3	3000	210.0	185.0	35.0

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